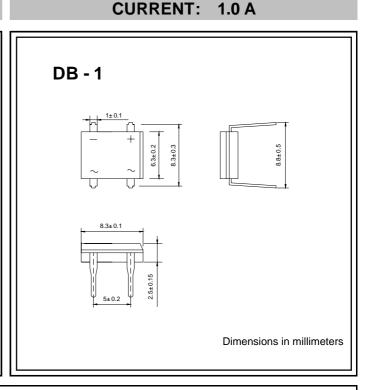
# SILICON BRIDGE RECTIFIERS

VOLTAGE RANGE: 50 --- 1000 V

## **FEATURES**

- ♦ Surge overload rating to 30 Amperes peak
- ♦ Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product

- Plastic material has UL flammability classification 94V-O
- Polarity symbols molded on body
- ♦ Weight: 0.016 ounces, 0.45 grams



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

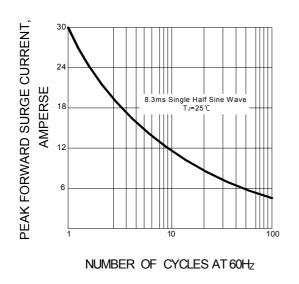
Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

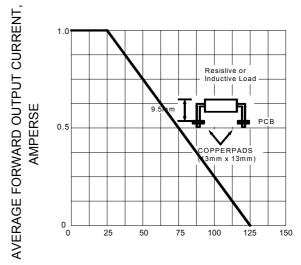
		DB101	DB102	DB103	DB104	DB105	DB106	DB107	UNITS
Maximum recurrent peak reverse voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Maximum average forw ard  Output current @T <sub>A</sub> =25℃	I <sub>F(AV)</sub>	1.0							А
Peak forw ard surge current  8.3ms single half-sine-wave superimposed on rated load	I <sub>FSM</sub>	30.0							А
Maximum instantaneous forward voltage at 1.0 A	V <sub>F</sub>	1.1						V	
Maximum reverse current @T <sub>A</sub> =25℃	I <sub>R</sub>	10.0							μΑ
at rated DC blocking voltage @T <sub>A</sub> =100℃		1.0							m A
Operating junction temperature range	$T_{J}$	- 55 + 150							$^{\circ}$
Storage temperature range	T <sub>STG</sub>	- 55 + 150							$^{\circ}$

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# FIG.1 - PEAK FORWARD SURGE CURRENT



# FIG.2 - FORWARD DERATING CURVE

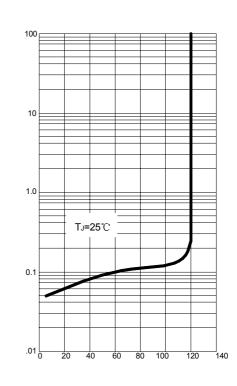


AMBIENT TEMPERATURE, °C

### FIG.3 - TYPICAL FORWARD CHARACTERISTIC

# 1.0 T<sub>J=125°C</sub> Pulse Width = 300us = 300us = 300us

### FIG.4 - TYPICAL REVERSE CHARACTERISTIC



INSTANTANEOUS FORWARD VOLTAGE, VOLTS

PERCENT OF RATED PEAK REVERSE VOLTAGE,%

2.

INSTANTANEOUS REVERSE CURRENT, MICRO AMPERSE